

Amendments to the Claims

Claims 1-7 (Cancelled)

- 5 8. (Currently Amended) The method of claim 20 wherein the step of applying a first conductive layer further comprises the step of applying a conductive layer with a temperature expansion coefficient similar to the cured polymer layer.
9. (Currently Amended) The method of claim 20 wherein the step of applying a
10 first conductive layer further comprises the step of applying a malleable conductor.

Claims 10-19 (Cancelled)

- 15 20. (Currently Amended) A method for creating an electron lens, comprising the steps of:
- applying a polymer layer on an emitter surface;
 - curing the polymer layer to reduce volatile content.
 - applying a first conductive layer on the polymer layer;
 - applying a photoresist layer on the first conductive layer;
 - 20 patterning the photoresist layer to define an electron lens;
 - etching the first conductive layer to create an opening; and
 - etching the polymer layer within the opening with a selective etch such that the ratio of etching of the polymer layer to the emitter surface is greater than 1000:1 wherein the etch profile has an undercut of about 1 micron to about 2
25 microns per about 6.5 microns of etch depth.

21. (Original) The method of claim 20 wherein the step of patterning the photoresist layer includes the step of patterning the photoresist layer to define a shield layer.

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22. (Original) The method of claim 20 wherein the photoresist layer is not removed before the step of etching the polymer layer with the selective etch.

23. (Original) The method of claim 20 wherein the polymer etch process conditions are set to balance the conditions between etch rate, etch residue, etch profile, and minimum DC bias.

5 Claim 24 (Cancelled)

25. (Original) An electron lens created by the process of claim 20.

26. (Original) A focused electron emitter created using the process of claim 20.

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Claims 27-40 (Cancelled)

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